



Supplement of

Re-evaluating the Frankfurt isothermal static diffusion chamber for ice nucleation

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1 Repeated wafer tests

In the table below the raw data and calculated relative and weighted errors for repetitious tests of wafers are presented. Eighteen wafers were measured with between two and ten repetitions at eight

temperature and saturation conditions (T, RH_i = -15 °C, 110 %; -20 °C, 120 %; -25 °C, 119 %; -25 °C, 126 %; -30 °C, 130 %; -30 °C, 132 %; -32 °C, 127 %; -32 °C, 134 %). This series of measurements resulted in 226 individual measurements, representing 87 wafer-saturation condition subsets. One wafer, saturation condition subset represents a single wafer repeatedly measured at a single saturation condition. For example, the measurement of wafer #1 at -15 °C and RH_i=110 % was repeated three times (see table below).

Relative error E_R is the percentage represented by the standard deviation σ_i of the mean INP counts \overline{INP}_i per subset *i*. Thus for *n* repetitions per wafer within a subset

$$\overline{INP}_i = \frac{\sum_{1}^{n} INP}{n},\tag{1}$$

where *INP* is the number of counts for an individual repetition and,

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$$E_R = \frac{\sigma_i}{\overline{INP}_i} \times 100.$$
 (2)

The weighted error E_W is the relative error normalized by the mean INP counts relative to the total INP counts for all subsets \overline{INP}_{all} , where

$$\overline{INP}_{all} = \sum_{i=1}^{87} \overline{INP}_i \text{ and}$$
(3)

$$E_W = \frac{\overline{INP}_i}{\overline{INP}_{all}} E_R.$$
(4)

- A total weighted error is calculated and presented at the conclusion of the table and within the text by summing the contributions from all of the individual subsets. In this case we have treated all of the available data and made no attempt to eliminate outliers, etc. We have chosen this approach in an attempt to maintain the broadest interpretation of reproducibility and to ensure wafers with low total counts cannot skew the error to be very large given small changes in absolute count. However, in other measurement contexts (e.g., a subset of the analyzed thermodynamic conditions) it may be
- valuable to re-examine and/or use some subset of the data. Thus we provide the entirety of the data set below.

Wafer	T (°C), RH _i (%)	Counts (INP)	Relative Error $(\%)$	Weighted Error $(\%)$
1	-15, 110	0	undefined	0
		0	(0)	
		0		
2	-15, 110	0	undefined	0
		0	(0)	
		0		
1	-20, 120	11	28.8	0.03
		20		
		16		
Wafer	$T(^{\circ}C), RH_{i}(\%)$	Counts (INP)	Relative Error (%)	Weighted Error (%)

Wafer	T (°C), RH _i (%)	Counts (INP)	Relative Error (%)	Weighted Error (%)
			21.9	
		37		
		29		
		20	28.1	0.02
		13		
		12		
		14		
		9		
		10		
		9		
		11		
		12		
		12		
18	-20, 120	24	23.7	0.02
		17		
		17		
		13		
		13		
		15		
		15		
		14		
		15		
		15		
1	-25, 119	3	20.2	0.004
		4		
2	-25, 119	90	9.5	0.06
		103		
3	-25, 119	3	91.5	0.05
,		14		
4	-25, 119	0	0	0
		0		
5	-25, 119	16	141.4	0.07
		0		
6	-25, 119	4	47.1	0.009
		2		
7	-25, 119	l r	94.3	0.02
8	-25, 119	3	20.2	0.004
		·	<u>-</u>	
9	-23, 119	1	4/.1	0.004
10	-23, 119	0	141.4	0.004
11	-23, 119	0	U	0
$ \frac{1}{12}$				
12	-23, 119	5	74.3	0.02
Wafer	$T(^{\circ}C)$ RH. (%)	$\frac{2}{Counts(INP)}$	$\frac{1}{\text{Relative Frror } (\%)}$	Weighted Error (%)
mater	$(\cup), \operatorname{KI}_{i}(\mathcal{D})$		Relative Lifer (70)	(70)

Wafer	$T(^{\circ}C), RH_{i}(\%)$	Counts (INP)	Relative Error (%)	Weighted Error (%)
		2		
		0 1	141.4	0.004
15				
	,,	9		
		13		
16	-25, 119	9	60.6	0.1
		31		
		41		
1	-25, 126	71	10.2	0.04
		82		
2	-25, 126	$-\bar{2}30$	3.1	0.04
		220		
3	-25, 126	93	38.7	0.2
,		$ \frac{53}{22}$		
4	-25, 126	28	72.0	0.3
		$ \frac{80}{0}$		
3	-23, 120	55	03.0	0.2
		20		
		$\frac{20}{33}$		
0	20,120	57	0,11	011
		45	56.6	
		105		
8	-25, 126	25	67.9	0.2
		19		
		64		
9	-25, 126	9	17.7	0.009
10	-23, 120	134	13.8	0.1
		$\frac{125}{20}$	47 1	
	23, 123	10	17.11	0.01
12		159	12.6	
		133		
13		19	10.3	0.01
		22		
14	-25, 126	10	15.7	0.009
15	-25, 126	93	20.5	0.1
		08 103		
		$ \frac{103}{168}$	204	
10	25, 120	210	20. T	0.2
		140		
17			12.1	
		22		
		25		
Wafer	T (°C), RH _i (%)	Counts (\overline{INP})	Relative Error (%)	Weighted Error (%)

Wafer	T (°C), RH _i (%)	Counts (INP)	Relative Error (%)	Weighted Error (%)
		26 26 27 23 25 30 27 18	71	
10	-23, 120	17 19 16 18 16 18 17 18 20	7.1	0.000
1	-30, 130	150 190	16.6	0.2
2	-30, 130	$\overline{240}$ 250	2.9	0.04
	-30, 130	$\overline{130}$	51.1	
6		<u>40</u> 80	47.1	0.2
	-30, 130	$\frac{1}{187}$	29.2	0.4
		$\begin{array}{c} 234\\ 12\\ 9\\ 28\end{array}$	62.5	
- 10 -		$\overline{412}$ $\overline{390}$	3.9	0.1
- 11		<u>1</u> 13 85		
12		$\overline{140}$	0.5	0.004
- 13 -	-30, 130	$\frac{105}{135} = $	3.2	
14	-30, 130	$\frac{129}{52} \frac{129}{52}$	10.2	0.03
- <u>ī</u> 5 -		$ \begin{array}{c} - & - & - & - & - & - & - & - & - & - &$	16.7	0.2
		144 255		
		188		
Wafer	T (°C), RH _i (%)	Counts (INP)	Relative Error (%)	Weighted Error (%)

Wafer	T (°C), RH _i (%)	Counts (INP)	Relative Error (%)	Weighted Error (%)
		163		
		192		
18		43	10.9	0.02
		41		
		35		
		34		
		33		
		33		
		33		
		32		
		35		
1	-30, 132	430	1.6	0.04
		440		
2		530		
		320		
4		702		
		786		
5	-30, 132	346	0.8	0.02
		350		
7	-30, 132	319	2.8	0.05
		332		
9		49	44.5	0.2
		94		
10	-30, 132	360	0.6	0.01
		357		
11		195	23.2	0.24
		140		
13	-30, 132	180	7.9	0.08
		161		
14	-30, 132	93	1.5	0.009
		91		
1	-32, 127	400	0	0
	,	400		
		$\bar{3}\bar{3}\bar{0}$		
		320		
		$\bar{1}6\bar{0}$		
		110		
		95		0.1
		68		
		8	0	0
		8		
6		51	32.1	0.1
		81		
7 - 7		204	2.7	
		212		
		27	32.3	
		43		
Wafer	T (°C), RH_i (%)	Counts (INP)	Relative Error (%)	Weighted Error (%)

Wafer	T (°C), RH _i (%)	Counts (INP)	Relative Error (%)	Weighted Error (%)
		19	102.9	0.07
		3		
10	-32, 127		11.4	0.2
		240		
11	-32, 127	31	45.1	0.07
		16		
12	-32, 127	101	36.0	0.2
		60		
13	-32, 127	$\frac{1}{23}$	52.3	0.1
		50		
14	-32, 127	12	5.7	0.004
		13		
1	-32, 134	1100	17.0	1.3
	,	1400		
		1150	17.3	
		900		
		1340		
		1900		
		741	22.7	
		536		
6		895	15.0	0.9
		1108		
7	-32, 134	475	10.0	0.3
		412		
10	-32, 134	701	9.8	
		610		
12	-32, 134	525	23.0	0.9
		729		
13	-32, 134	250	0.3	0.004
		251		
14	-32, 134	-235	26.9	0.3
		160		
				$\sum = 16.1 \sim 20$
Wafer	T (°C), RH _i (%)	Counts (INP)	Relative Error (%)	Weighted Error (%)

2 Saharan dust event

On April 16, 2015 a Saharan dust event was observed at the Taunus Observatory, Mt. Kleiner Feldberg (826 m msl, 50.221879° N, 8.446297° E). Figures 1 and 2 show the temporal evolution of the dust transport event in six hour increments. In Fig. 1 (a) and (b) the dust layer is primarily west of the Spanish and French coast and by 00 UTC on April 16 (Fig. 1 (c)) dust begins to pervade wide areas of central Europe. Figures 2 (d), (e) and (f) confirm that dust is present throughout the entire day, albeit within the RGB product the dust layer is superimposed with cold thick high-level clouds (red) and low-level clouds (yellow) and thus is not always clearly visible.

Figure 3 is the BSC-DREAM8b (vid BSC-DREAM8b ref., and Basart et al., 2012) modeled vertical profile of dust on April 16, 2015 above Taunus Observatory. It highlights that dust was present throughout the day, even in the lowest kilometer of the atmosphere. Thus it is reasonable to conclude that atmospheric samples taken at Taunus Observatory on April 16, 2015 included Saharan

40 dust. Back trajectories from 12 UTC April 16, 2015 computed using HYSPLIT (Draxler and Rolph, 2015; Rolph, 2015) and arriving at the Taunus Observatory, confirm the observation that the local air mass advanced from the Saharan region (Fig. 4).



Figure 1. Temporal evolution of the Saharan dust event from (a) 12 UTC April 15, 2015 to (c) 00 UTC April 16, 2015. The lefthand panels show the dust load $(g/m^2, calculated using BSC-DREAM8b)$, while the right-hand panels show the EUMETSAT RGB dust product, with the intensity of the magenta corresponding to dust intensity.







Figure 2. Continuation of Fig. 1's temporal evolution of the Saharan dust event from (d) 06 UTC April 1, 2015 to (f) 18 UTC April 16, 2015. Again the lefthand panels show the dust load $(g/m^2, calculated using BSC-DREAM8b)$, while the righthand panels show the EUMETSAT RGB dust product, with the intensity of the magenta corresponding to dust intensity.

0.25



Figure 3. Vertical profile of dust concentration above Taunus Observatory on April 16, 2015 calculated using BSC-DREAM8b.



Figure 4. Back trajectories originating from Taunus Observatory at 1000 m (red), 2000 m (blue) and 3000 m (green) amsl. Trajectories were initiated at 12 UTC April 16 2015 and run for 240 hours.

References

Basart, S., Pérez, C., Nickovic, S., Cuevas, E., and Baldasano, J.: Development and evaluation of the BSC-

- 45 DREAM8b dust regional model over Northern Africa, the Mediterranean and the Middle East, Tellus B, 64, 2012.
 - BSC-DREAM8b: Data and/or images from the BSC-DREAM8b (Dust REgional Atmospheric Model) model, operated by the Barcelona Supercomputing Center (http://www.bsc.es/projects/earthscience/BSC-DREAM/).
- 50 Draxler, R. R. and Rolph, G. D.: HYSPLIT (HYbrid Single-Particle Lagrangian Integrated Trajectory) Model access via NOAA ARL READY Website (http://ready.arl.noaa.gov/HYSPLIT.php), NOAA Air Resources Laboratory, Silver Spring, MD, 2015.
 - Rolph, G. D.: Real-time Environmental Applications and Display sYstem (READY) Website (http://ready.arl. noaa.gov), NOAA Air Resources Laboratory, Silver Spring, MD, 2015.